

No.4718A

PNP Epitaxial Planar Silicon Transistor

DC/DC Converter,

Motor Driver Applications

## **Features**

- · Adoption of FBET and MBIT processes.
- · Large current capacity.
- · Low collector-to-emitter saturation voltage.
- · Small size making it easy to provide high-density, small-sized hybrid ICs.

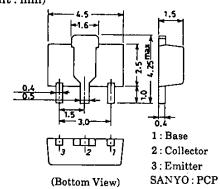
Absolute Maximum Ratings at Ta = 25°C			unit	
Collector-to-Base Voltage	$V_{CBO}$		-25 V	
Collector-to-Emitter Voltage	$V_{CEO}$		-20 V	
Emitter-to-Base Voltage	VEBO		-7 V	
Collector Current	$I_{\mathbb{C}}$		-2.5 A	
Collector Current (Pulse)	I <sub>CP</sub>		-5 A	
Collector Dissipation	$P_{C}$	Mounted on ceramic board (250mm <sup>2</sup> ×0.8mm)	1.3 W	
Junction Temperature	Tj		150 °C	
Storage Temperature	Tstg		-55 to +150 °C	
Electrical Characteristics at Ta = 25°C			min typ max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$	-100	nA (
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -6V, I_{C} = 0$	-100	nA (
DC Current Gain	$h_{FE}(1)$	$V_{CE} = -2V_{IC} = -0.5A$	140% 400	) <b>※</b>
	$h_{FE}(2)$	$V_{CE} = -2V, I_{C} = -2.5A$	70	
Gain-Bandwidth Product	$f_{T}$	$V_{CE} = -2V, I_{C} = -0.3A$	400	MHz
Output Capacitance	Cob	$V_{CB} = -10V$ , $f = 1MHz$	26	$\mathbf{pF}$
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -30mA$	-220 -400	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -1.5A, I_B = -30mA$	-0.9 -1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_{\rm C} = -10 \mu A, I_{\rm E} = 0$	-25	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1 \text{mA}, R_{BE} = \infty$	-20	V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-7	V
$\times$ The 2SA1896 is classified by 0.5A h <sub>FE</sub> as follows:				
140 C 000 T 40	$\overline{}$			

140 S 280 200 T 400

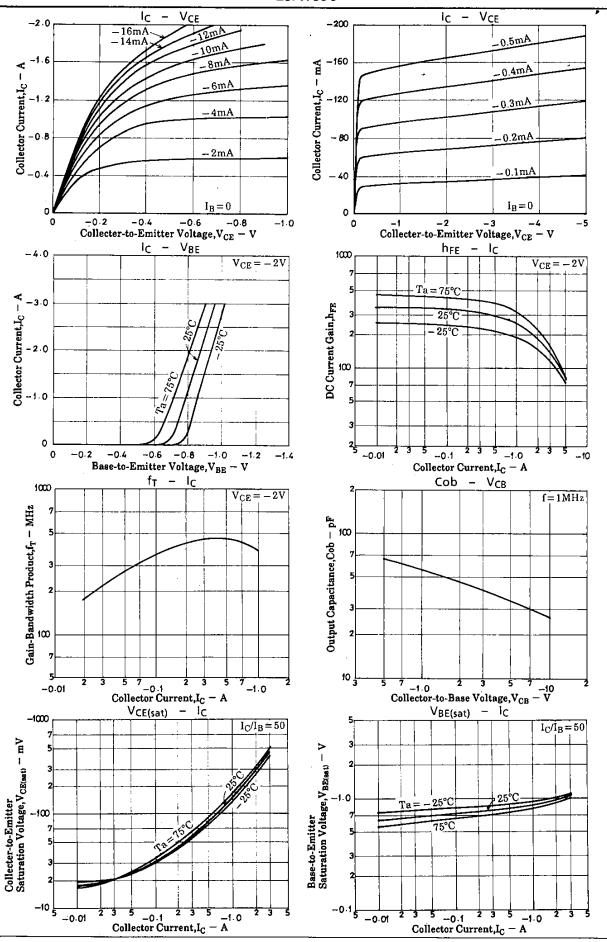
Marking: AM hFE rank: S, T

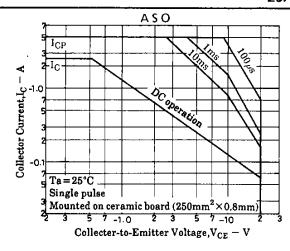
## Package Dimensions 2038A

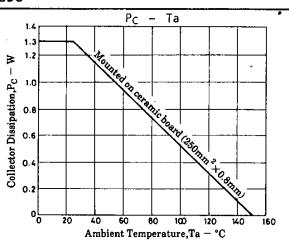
(unit: mm)



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